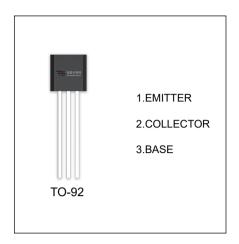


**2SA562** TRANSISTOR (PNP)

### **FEATURES**

• Excellent h<sub>FE</sub> Linearlity



### **ORDERING INFORMATION**

Part Number	Package	Packing Method	Pack Quantity
2SA562	TO-92	Bulk	1000pcs/Bag
2SA562-TA	TO-92	Таре	2000pcs/Box

## MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V <sub>CBO</sub>	Collector-Base Voltage	-35	6	
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	6	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	6	
Ic	Collector Current -Continuous	-500	MA	
Pc	Collector Power Dissipation	500	M7	
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range -55~+150 °C			



# $T_a$ =25 $^{\circ}$ C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V(BR) <sub>CBO</sub>	Ic=-100μA, IE=0	-35			6
Collector-emitter breakdown voltage	V(BR) <sub>CEO</sub>	Ic=-1mA, IB=0~30				6
Emitter-base breakdown voltage	V(BR) <sub>EBO</sub>	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5			6
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =35V, I <sub>E</sub> =0			-0.1	<b>⋈</b> A
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.1	<b>⊠</b> A
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA	70		240	
Collector-emitter saturation voltage	V <sub>CE(SAT)</sub>	Ic=-100mA, I <sub>B</sub> =-10mA			-0.25	6
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA			-1	6
Transition frequency	f⊤	V <sub>CE</sub> =-6V, I <sub>C</sub> =-20mA		200		M(Z
Collector output capacitance	C <sub>ob</sub>	V <sub>CE</sub> =-6V, I <sub>E</sub> =0,f=1MHz	13			pF

## **CLASSIFICATION OF hfe**

RANK	0	Υ
RANGE	70-140	120-240



